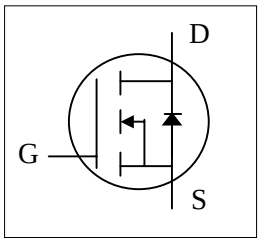
N-CHANNEL ENHANCEMENT MODE POWER MOSFET

PRODUCT SUMMARY

Simple Drive Requirement
Lower On-resistance
Fast Switching Characteristic
RoHS Compliant

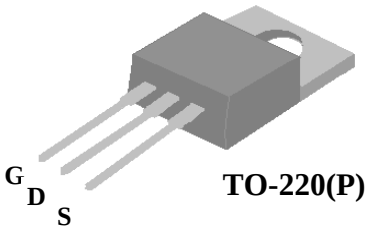


BV_{DSS}	75V
$R_{DS(ON)}$	5mΩ
I_D	80A

DESCRIPTION

The advanced power MOSFETs from Silicon Standard Corp. provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial power applications and suited for low voltage applications such as DC/DC converters.



TO-220(P)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	75	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[3]	80	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V	70	A
I_{DM}	Pulsed Drain Current[1]	320	A
P_D@T_C=25℃	Total Power Dissipation	300	W
	Linear Derating Factor	2	W/℃
E_{AS}	Single Pulse Avalanche Energy[4]	450	mJ
T_{STG}	Storage Temperature Range	-55 to 175	℃
T_J	Operating Junction Temperature Range	-55 to 175	℃

THERMAL DATA

Symbol	Parameter		Value	Units
Rthj-c	Thermal Resistance Junction-case	Max.	0.5	℃/W
Rthj-a	Thermal Resistance Junction-ambient	Max.	62	℃/W

ELECTRICAL CHARACTERISTICS

(T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=1mA	75	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I_D=1mA	-	0.01	-	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=60A	-	-	5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	4	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=60A	-	57	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=75V, V_{GS}=0V	-	-	10	uA
	Drain-Source Leakage Current (T_j=150°C)	V_{DS}=60V ,V_{GS}=0V	-	-	250	uA
I_{GSS}	Gate-Source Leakage	V_{GS}= ±20V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=80A	-	85	135	nC
Q_{gs}	Gate-Source Charge	V_{DS}=40V	-	25	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=10V	-	36	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=40V	-	22	-	ns
t_r	Rise Time	I_D=80A	-	160	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω,V_{GS}=10V	-	38	-	ns
t_f	Fall Time	R_D=0.5Ω	-	165	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	4290	6870	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	985	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	390	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.2	1.8	Ω

SOURCE-DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=60A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time[2]	I_S=40A, V_{GS}=0V	-	75	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	190	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Package limitation current is 80A, calculated continuous current based on maximum allowable junction temperature is 169A.

4.Starting T_j=25°C , L=1mH , I_{AS}=30A.

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.

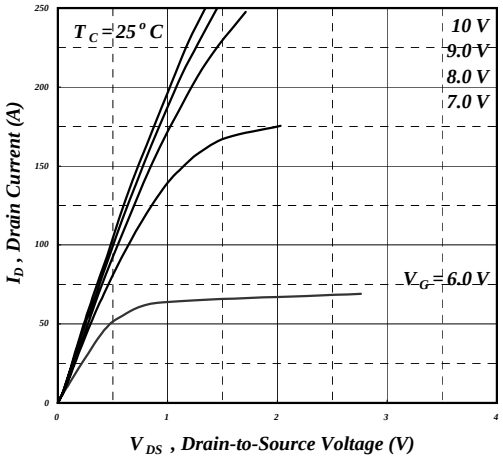


Fig 1. Typical Output Characteristics

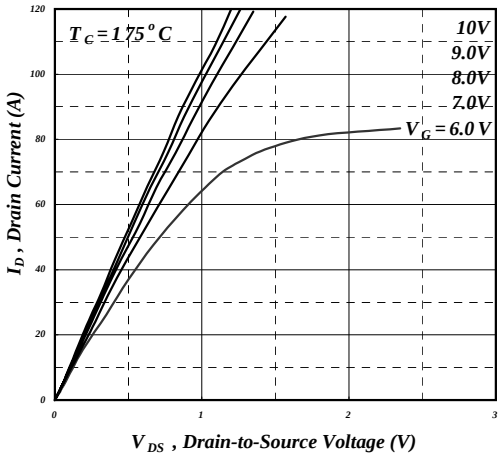


Fig 2. Typical Output Characteristics

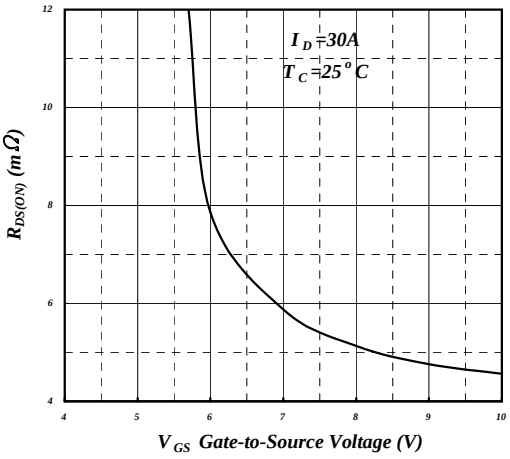


Fig 3. On-Resistance v.s. Gate Voltage

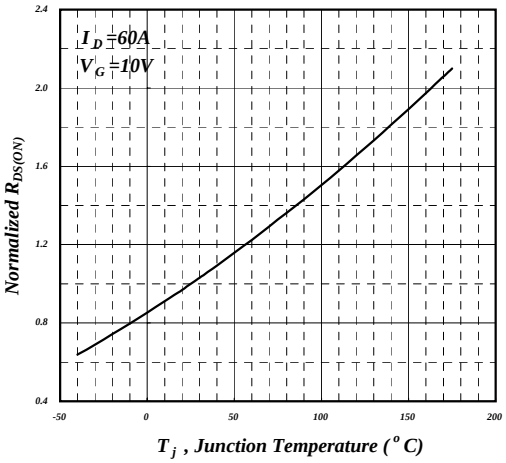


Fig 4. Normalized On-Resistance v.s. Junction Temperature

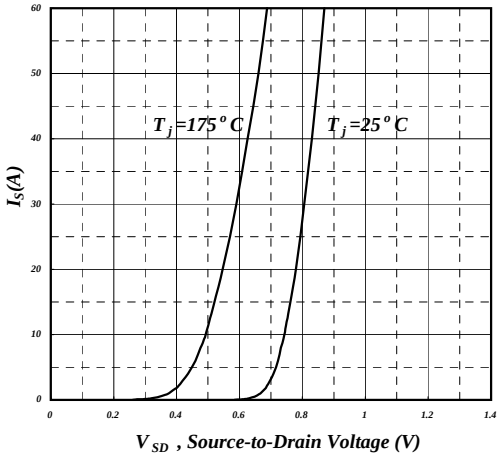


Fig 5. Forward Characteristic of Reverse Diode

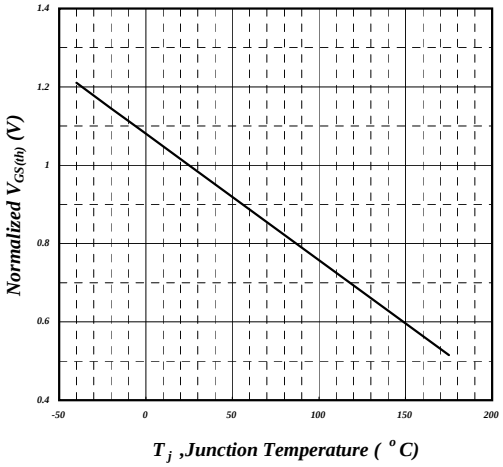


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

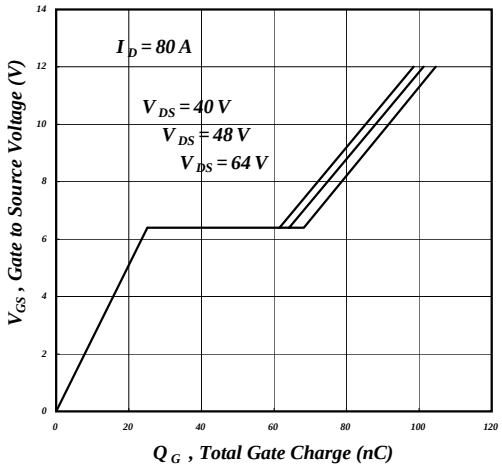


Fig 7. Gate Charge Characteristics

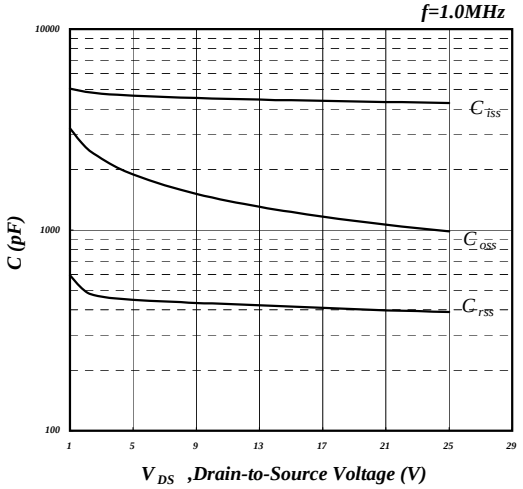


Fig 8. Typical Capacitance Characteristics

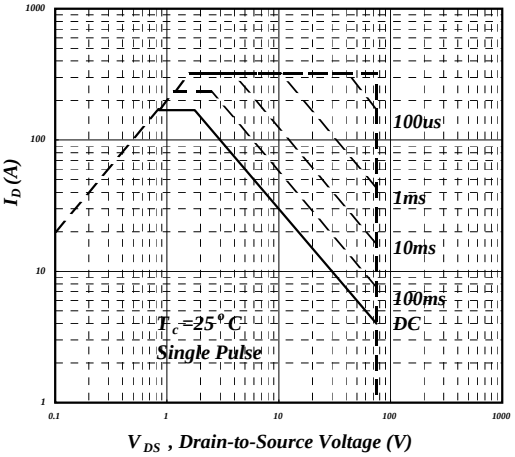


Fig 9. Maximum Safe Operating Area

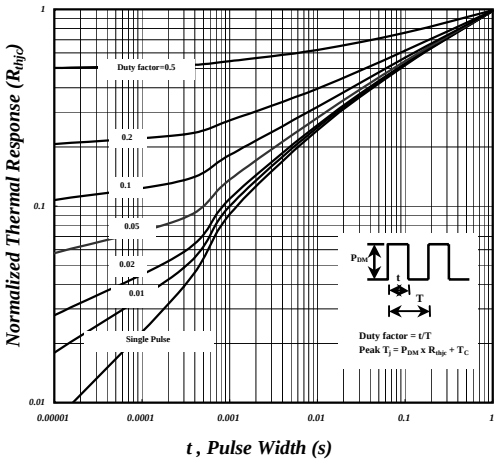


Fig 10. Effective Transient Thermal Impedance

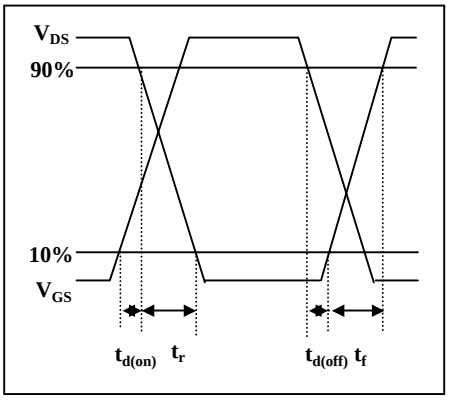


Fig 11. Switching Time Waveform

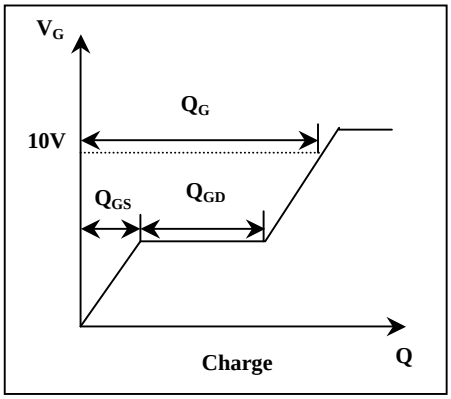
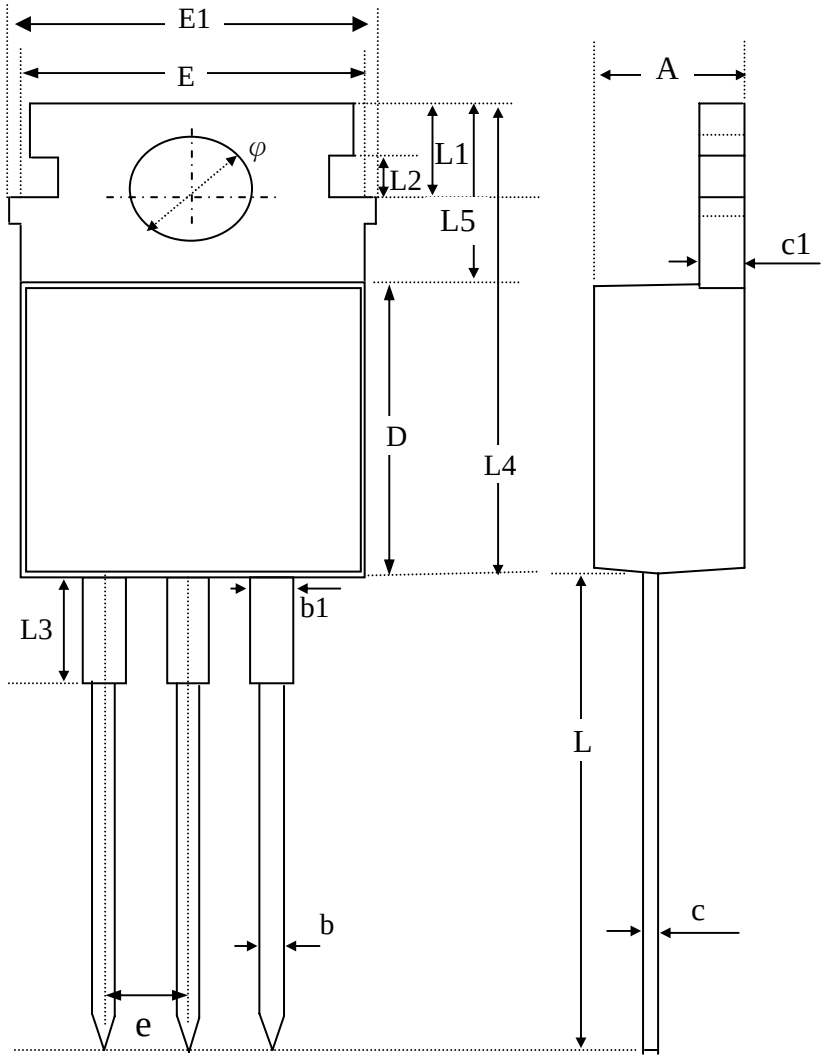


Fig 12. Gate Charge Waveform

Package Outline : TO-220



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.25	4.48	4.70
b	0.65	0.80	0.90
b1	1.15	1.38	1.60
c	0.40	0.50	0.60
c1	1.00	1.20	1.40
E	9.70	10.00	10.40
E1	---	---	11.50
e	----	2.54	----
L	12.70	13.60	14.50
L1	2.60	2.80	3.00
L2	1.00	1.40	1.80
L3	2.6	3.10	3.6
L4	14.70	15.50	16
L5	6.30	6.50	6.70
φ	3.50	3.60	3.70
D	8.40	8.90	9.40

1.All Dimensions Are in Millimeters.

2.Dimension Does Not Include Mold Protrusions.

Part Marking Information & Packing : TO-220